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ATTY DOCKET NO.
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SERIAL NO. 10/654 404
NEW

Knut Beekman et al.

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September 4, 2003

GROUP
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U.S. PATENT DOCUMENTS

EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
<i>HL</i>	A	5,242,860	09/1993	NULMAN et al.			
<i>HL</i>	B	5,523,259	06/1996	MERCHANT et al.			
<i>HL</i>	C	5,278,448	01/1994	FUJII			
<i>HL</i>	D	5,843,843	12/1998	LEE et al.			
<i>HL</i>	E	5,462,890	10/1995	HWANG et al.			
<i>HL</i>	F	6,143,128	11/2000	AMEEN et al.			
<i>HL</i>	G	5,204,192	03/2001	ZHAO et al.			
<i>HL</i>	H	6,077,571	06/2000	KALOYEROS et al.			
<i>HL</i>	I	5,899,720	05/1999	MIKAGI			
<i>HL</i>	J	5,591,663	01/1997	NASU et al.			
<i>HL</i>	K	5,851,917	12/1998	LEE			

FOREIGN PATENT DOCUMENTS

		DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION	
							YES	NO
<i>HL</i>	L	11040518	02/1999	JAPAN				
<i>HL</i>	M	8274076	10/1996	JAPAN				
<i>HL</i>	N	7142412	06/1995	JAPAN				
<i>HL</i>	O	JP-9246212-A	09/1997	JAPAN				
<i>HL</i>	P	WO 88/02033	03/1998	PCT				

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)

<i>HL</i>	Q	C.R. Aita, "Basal orientation aluminum nitride grown...", J. Appl. Phys. 53(3), March 1982, pages 1807-1808.
<i>HL</i>	R	Hwan-Chul Lee et al., "Effects of sputtering pressure and nitrogen concentration on the preferred orientation of AlN thin films," Journal of Materials Science: Materials in Electronics (1994) 221-225.

EXAMINER *HL*

DATE CONSIDERED 5. 10. 2004

*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

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HL	S	H1792-B2	04/1999	MORAN et al.			
HL	T	4,959,136	09/1990	HATWAR			
HL	U	4,957,604	09/1990	STEININGER			
HL	V	6,001,736	12/1999	KONDO et al.			
HL	W	5,795,823	08/1998	AVANZINO et al.			
HL	X	6,025,762	02/2000	ROY et al.			

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							YES	NO
HL	Y	0 327 888 A2	08/1989	EPO				
HL	Z	0 583 736 A1	02/1994	EPO				
HL	AA	2 266 897 A	11/1993	UK				

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HL	BB	Hiroshi Okano et al., "Preparation of C-Axis Oriented AlN Thin Films by Low-Temperature Reactive Sputtering," Jpn. J. Appl. Phys. Vol. 31 (1992), Pt. 1, No. 10, pages 3446-3451.

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